Power MOSFET 1500V, 10.5Ω, 2.5A, N-Channel

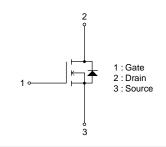


ON Semiconductor®

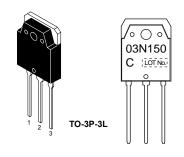
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VDSS	R _{DS} (on) Max	I _D Max	
1500V	10.5Ω@10V	2.5A	

ELECTRICAL CONNECTION N-Channel



MARKING



ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

Features

- Low On-Resistance
- Ultra High Voltage
- High Speed Switching
- 100% Avalanche Tested
- Pb-Free and RoHS compliance

Typical Applications

- Switch mode power supply
- AC Drive

SPECIFICATIONS

ABSOLUTE MAXIMUM RATINGS at Ta = 25°C (Note 1, 2, 3, 4)

Parameter	Symbol	Value	Unit	
Drain to Source Voltage		VDSS	1500	V
Gate to Source Voltage		VGSS	±30	V
Drain Current (DC)		ID	2.5	Α
Drain Current (Pulse) PW≤10µs, duty cycle≤1%		IDP	5	Α
Power Dissipation		PD	2.5	W
	Tc=25°C	טין	140	
Junction Temperature	Tj	150	°C	
Storage Temperature	Tstg	-55 to +150	°C	
Avalanche Energy (Single P	EAS	34	mJ	
Avalanche Current (Note 3)	IAV	2.5	Α	

Note 1: Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

Note 2: V_{DD}=50V, L=10mH, I_{AV}=2.5A (Fig.1)

Note 3 : L≤10mH, Single Pulse

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Value	Unit	
Junction to Case Steady State	$R_{\theta JC}$	0.89	0000	
Junction to Ambient (Note 4)	$R_{\theta JA}$	50.0	°C/W	

Note 4: Insertion mounted

ELECTRICAL CHARACTERISTICS at Ta = 25°C (Note 5, 6, 7)

Parameter	Cymbal	Conditions	Value			Unit	
Parameter	Symbol	Conditions	min	typ	max	Uill	
Drain to Source Breakdown Voltage	V(BR)DSS	ID=10mA, VGS=0V	1500			V	
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =1200V, V _{GS} =0V			1	mA	
Gate to Source Leakage Current	IGSS	V _{GS} =30V, V _{DS} =0V			±100	nA	
Gate Threshold Voltage	VGS(th)	V _{DS} =10V, I _D =1mA	2		4	>	
Forward Transconductance	gFS	V _{DS} =20V, I _D =1.25A		1.9		S	
Static Drain to Source On-State Resistance	R _{DS} (on)	I _D =1.25A, V _{GS} =10V		8	10.5	Ω	
Input Capacitance	Ciss			650		pF	
Output Capacitance	Coss	V _{DS} =30V, f=1MHz		70		pF	
Reverse Transfer Capacitance	Crss			20		pF	
Turn-ON Delay Time	t _d (on)			15		ns	
Rise Time	t _r	One Fire O		24		ns	
Turn-OFF Delay Time	t _d (off)	See Fig.2		140		ns	
Fall Time	tf			47		ns	
Total Gate Charge	Qg			34		nC	
Gate to Source Charge	Qgs	V _{DS} =200V, V _{GS} =10V, I _D =2.5A		4.7		nC	
Gate to Drain "Miller" Charge	Qgd			15		nC	
Forward Diode Voltage	V _{SD}	IS=2.5A, VGS=0V		8.0	1.5	V	
Reverse Recovery Time	trr	See Fig.3		350		ns	
Reverse Recovery Charge	Qrr	IS=2.5A, VGS=0V, di/dt=100A/μs		2220		nC	
Effective Output Capacitance, Energy Related (Note 6)	Co(er)	VGS=0V, VDS=0 to 1200V		18.3		pF	
Effective Output Capacitance, Time Related (Note 7)	Co(tr)	VG5-0V, VD5-0 to 1200V		29.6		pF	

Note 5 : Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

Note 6 : Co(er) is a fixed capacitance that gives the same stored energy as Coss while VDS is rising from 0 to 80% V(BR)DSS.

Note 7: Co(tr) is a fixed capacitance that gives the same charging time as Coss while VDS is rising from 0 to 80% V(BR)DSS.

Fig. 1 Unclamped Inductive Switching Test Circuit

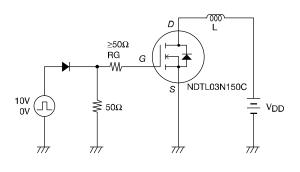


Fig. 2 Switching Time Test Circuit

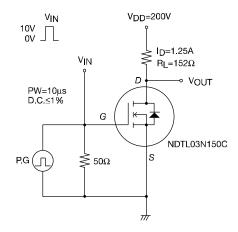
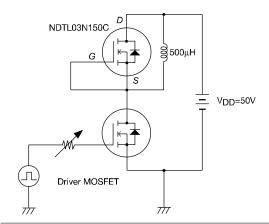
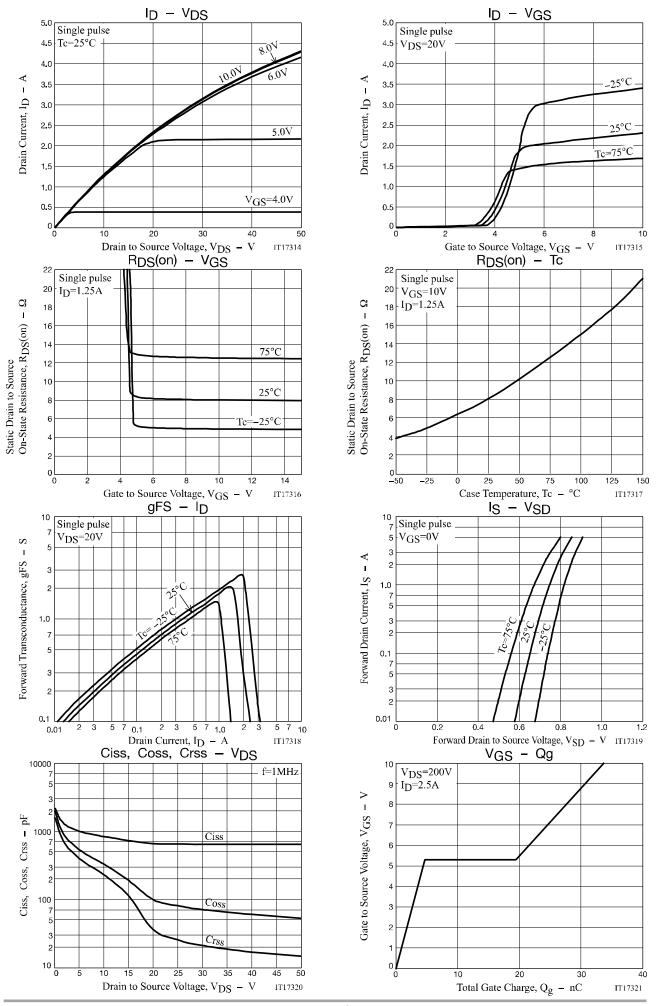
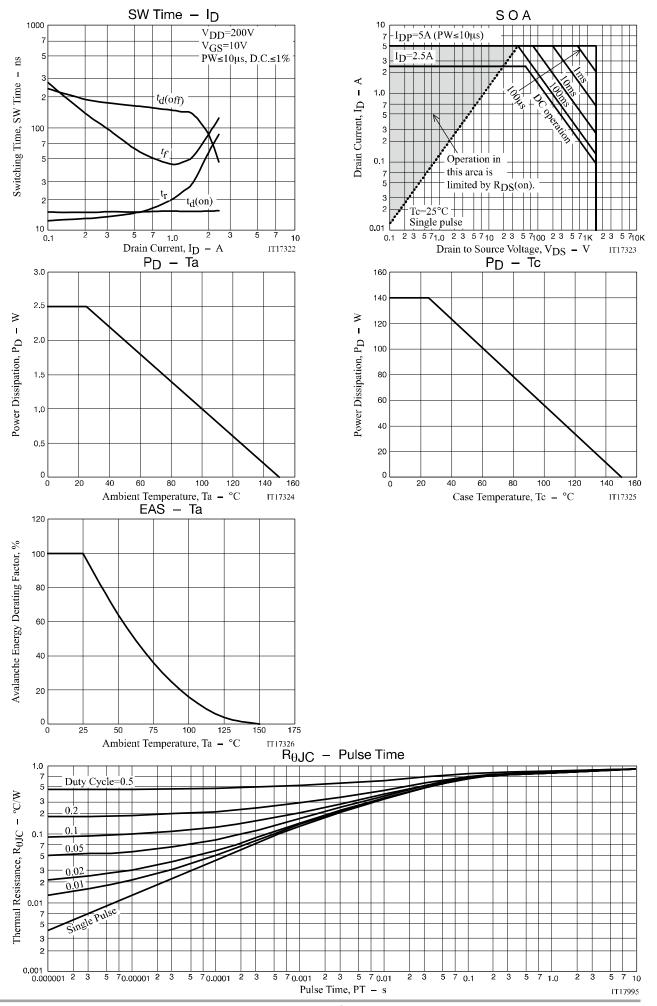


Fig. 3 Reverse Recovery Time Test Circuit

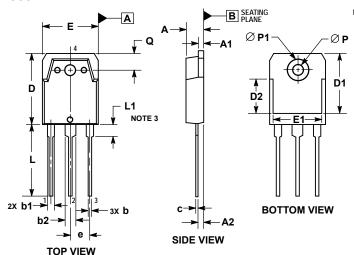






PACKAGE DIMENSIONS

unit: mm TO-3P-3L CASE 340AF **ISSUE A**



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.

CONTROLLING DIMENSION: MILLIMETERS
CONTOUR UNCONTROLLED IN THIS AREA
DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR GATE
PROTRUSIONS. MOLD FLASH OR GATE PROTRUSIONS NOT TO EXCEED 0.13 PER SIDE. THESE DIMENSIONS ARE TO BE MEA SURED AT THE OUTERMOST EXTREME OF THE PLASTIC BODY. DIMENSIONS b1 AND b2 OO NOT INCLUDE DAMBAR PROTRUSION. DAMBAR PROTRUSION SHALL NOT EXCEED 0.10.

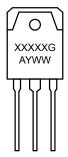
SIGN. DANIDARY I ROTROSION SIT						
	MILLIMETERS					
DIM	MIN	NOM	MAX			
Α	4.60	4.80	5.00			
A1	1.45	1.50	1.65			
A2	1.20	1.40	1.60			
b	0.80	1.00	1.20			
b1	1.80	2.00	2.20			
b2	2.80	3.00	3.20			
С	0.55	0.60	0.75			
D	19.70	19.90	20.10			
D1	16.56	16.76	16.96			
D2	9.80	10.00	10.20			
E	15.40	15.60	15.80			
E1	13.40	13.60	13.80			
е	5.15	5.45	5.75			
L	19.80	20.00	20.20			
L1	3.30	3.50	3.70			
Р	3.00	3.20	3.40			
P1	6.80	7.00	7.20			
0	4.80	5.00	5.20			

1: Gate

2: Drain

3: Source

GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code

Α = Assembly Location

Υ = Year WW = Work Week G = Pb-Free Package

ORDERING INFORMATION

Device	Device Marking		Shipping (Qty / Packing)	
NDTL03N150CG	03N150C	TO-3P-3L (Pb-Free)	30 / Tube	

Note on usage: Since the NDTL03N150C is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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^{*}This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G", may or not be present.

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